

ABSTRACT

A variable capacitance formed in a semiconductor substrate with a ribbed surface, having a first electrode formed of all the ribs protruding from the substrate, of portions of the substrate underlying the ribs, and of at least portions of the substrate separating the
5 bases of two ribs, having a second electrode superposed to at least one portion of the first electrode. The ribs are irregular in terms of cross-section and/or planar base surface area.